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# P-Channel 12 V (D-S) MSOSFET

### **DESCRIPTION**

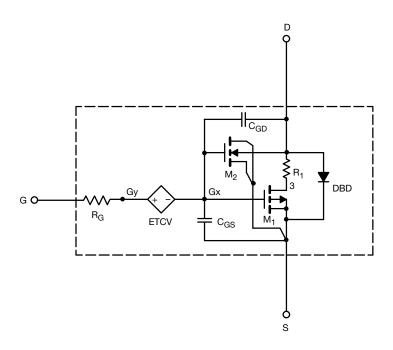
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the -  $55\,^{\circ}$ C to +  $125\,^{\circ}$ C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



## Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |   |                |                  |      |
|--|---------------------|---|----------------|------------------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   | SIMULATED DATA | MEASURED<br>DATA | UNIT |
| Static   |                     |   |                |                  |      |
| Gate-Source Threshold Voltage  | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$                                | 80             | -                | V    |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 1.5 A                     | 0.022          | 0.022            | Ω    |
|  |                     | V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 1.5 A                     | 0.029          | 0.028            |      |
| Forward Transconductance <sup>a</sup>                                  | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 6 V, I <sub>D</sub> = - 1.5 A                       | 11             | 10               | S    |
| Diode Body Voltage   | V <sub>SD</sub>     | I <sub>S</sub> = - 1.5 A  | 0.7            | - 0.8            | V    |
| Dynamic <sup>b</sup>   |                     |   |                |                  |      |
| Input Capacitance  | C <sub>iss</sub>    | V <sub>DS</sub> = -6 V, V <sub>GS</sub> = 0 V, f = 1 MHz                | 1840           | 1840             | pF   |
| Output Capacitance   | C <sub>oss</sub>    |   | 424            | 410              |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |   | 380            | 380              |      |
| Total Gate Charge  | 0                   | $V_{DS} = -6 \text{ V}, V_{GS} = 10 \text{ V}, I_D = -1.5 \text{ A}$    | 33             | 43               | nC   |
|  | Qg                  | V <sub>DS</sub> = -6 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = -1.5 A | 17             | 21               |      |
| Gate-Source Charge   | $Q_{gs}$            |   | 2.1            | 2.1              |      |
| Gate-Drain Charge  | Q <sub>gd</sub>     |   | 4.8            | 4.8              |      |

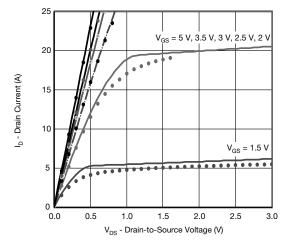
#### Notes

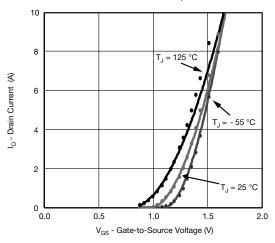
- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

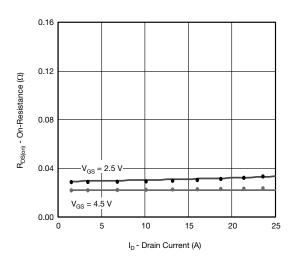
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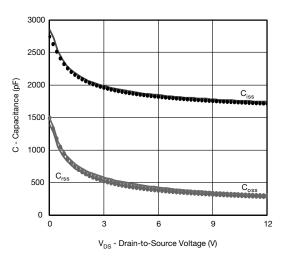
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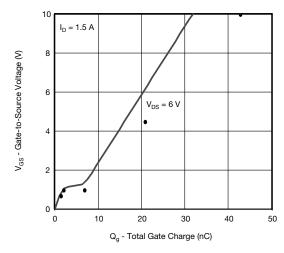
# **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25~^{\circ}C$ , unless otherwise noted)

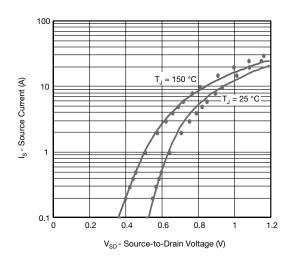












#### Note

Dots and squares represent measured data.
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